

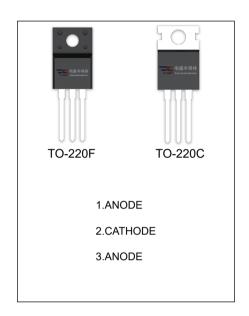
SBD30130SCTB SBDF30130SCTB SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

Io	30 (2×15) A
V_{RRM}	130 V
T _j	150 ℃
$V_{F(typ)}$	0.66V (@Tj=125℃)

FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

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Symbol	Parameter		F30130SCTB	Unit	
V _{RRM}	Peak repetitive reverse voltage				
V _{RWM}	Working peak reverse voltage		130		
V _R	DC blocking voltage				
V _{R(RMS)}	RMS reverse voltage	91		V	
lo	Average rectified output current	30		Α	
I _{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)	200		Α	
R _{OJc}	Thermal resistance from junction to case ,Tc=25℃	2.0	3.0	°C/W	
R _{OJA}	Thermal resistance from junction to ambient	62.5		°C/W	
Tj	Junction temperature	150		$^{\circ}$	
T _{stg}	Storage temperature	-55~+150		℃	

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions I _R =1mA		Min 130	Тур	Max	Unit V
Reverse voltage	V _(BR)						
Reverse current	I _R	V _R =130V	Tj =25℃		15	100	uA
			Tj =125℃		10		mA
Forward voltage	V _F	I _F =10A	Tj =25℃		0.66		V
			Tj =125℃		0.59		V
		I _F =15A	Tj =25℃		0.78	0.82	V
		1F-13A	Tj =125℃		0.66		V

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



